

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP1520 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

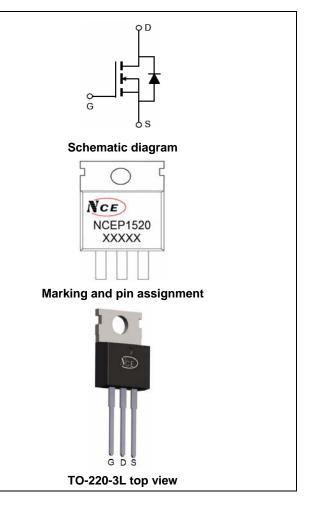
General Features

- V_{DS} =150V, I_D =20A $R_{DS(ON)}$ =59m Ω (typical) @ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- LED backlighting
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED! 100% ΔVds TESTED!



Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|----------|----------------|-----------|------------|----------|
| NCEP1520 | NCEP1520 | TO-220-3L | - | - | - |

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|-----------------------|------------|----------------------|
| Drain-Source Voltage | V_{DS} | 150 | V |
| Gate-Source Voltage | V_{GS} | ±20 | V |
| Drain Current-Continuous | I _D | 20 | А |
| Drain Current-Continuous(T _C =100°C) | I _D (100℃) | 14 | Α |
| Pulsed Drain Current | I _{DM} | 80 | Α |
| Maximum Power Dissipation | P _D | 68 | W |
| Derating factor | | 0.45 | W/℃ |
| Single pulse avalanche energy (Note 5) | E _{AS} | 65 | mJ |
| Drain Source voltage slope, V _{DS} ≤120 V, | dv/dt | 50 | V/ns |
| Drain Source voltage slope, V _{DS} ≤120 V, I _{SD} <i<sub>D</i<sub> | dv/dt | 50 | V/ns |
| Operating Junction and Storage Temperature Range | T_{J} , T_{STG} | -55 To 175 | $^{\circ}\mathbb{C}$ |



Thermal Characteristic

| Thermal Résistance, Junction-to-Case ^(Note 2) | $R_{	heta JC}$ | 2.2 | °C/W |
|--|----------------|-----|------|
|--|----------------|-----|------|

Electrical Characteristics (T_A=25 [°]C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|------------------------------------|---------------------|---|-----|------|------|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250μA | 150 | - | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =150V,V _{GS} =0V | - | - | 1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V_{GS} =±20 V , V_{DS} =0 V | - | - | ±100 | nA |
| On Characteristics (Note 3) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS}=V_{GS}$, $I_{D}=250\mu A$ | 2.5 | 3.3 | 4.5 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =10A | - | 59 | 65 | mΩ |
| Gate resistance | R _G | | - | 4.5 | - | Ω |
| Forward Transconductance | G FS | V _{DS} =5V,I _D =10A | 15 | - | - | S |
| Dynamic Characteristics (Note4) | · | | | | | |
| Input Capacitance | C _{lss} | \\ 75\\\\ 0\\ | - | 600 | | PF |
| Output Capacitance | C _{oss} | V_{DS} =75V, V_{GS} =0V, F=1.0MHz | - | 74.7 | | PF |
| Reverse Transfer Capacitance | C _{rss} | r=1.0lvlm2 | - | 10.8 | | PF |
| Switching Characteristics (Note 4) | | | | | | |
| Turn-on Delay Time | t _{d(on)} | | - | 9.5 | - | nS |
| Turn-on Rise Time | t _r | V_{DD} =75 V , R_L =7.5 Ω | - | 5.5 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | V_{GS} =10 V , R_{G} =3 Ω | - | 12.5 | - | nS |
| Turn-Off Fall Time | t _f | | - | 3 | - | nS |
| Total Gate Charge | Qg | \/ -75\/ -104 | - | 12 | - | nC |
| Gate-Source Charge | Q _{gs} | V_{DS} =75 V , I_{D} =10 A , V_{GS} =10 V | - | 2.8 | - | nC |
| Gate-Drain Charge | Q_{gd} | VGS-10V | - | 1.8 | - | nC |
| Drain-Source Diode Characteristics | · | | | | | |
| Diode Forward Voltage (Note 3) | V _{SD} | V _{GS} =0V,I _S =10A | - | - | 1.2 | V |
| Diode Forward Current (Note 2) | Is | | - | - | 20 | Α |
| Reverse Recovery Time | t _{rr} | $T_J = 25^{\circ}C, I_F = I_S$ | - | 29 | - | nS |
| Reverse Recovery Charge | Qrr | $di/dt = 100A/\mu s^{(Note3)}$ | - | 130 | - | nC |

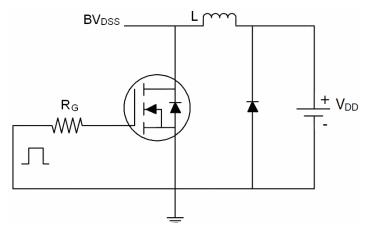
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, $t \leq 10 \mbox{ sec.}$
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25 Ω

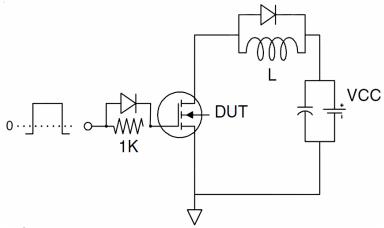


Test Circuit

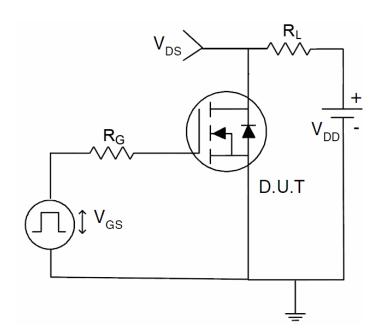
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics

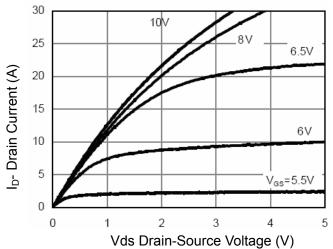


Figure 1 Output Characteristics

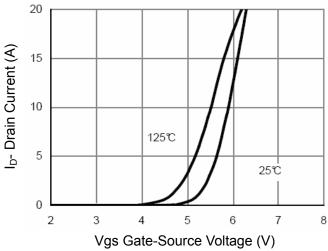


Figure 2 Transfer Characteristics

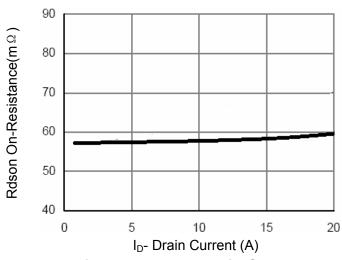


Figure 3 Rdson- Drain Current

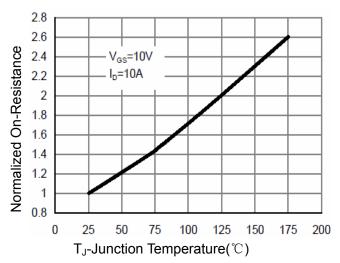


Figure 4 Rdson-Junction Temperature

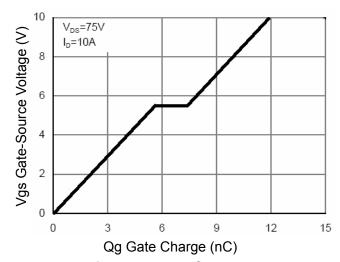


Figure 5 Gate Charge

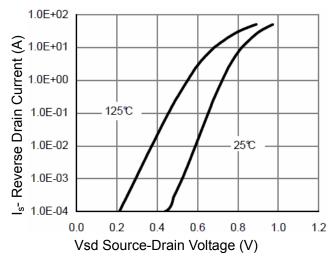


Figure 6 Source- Drain Diode Forward



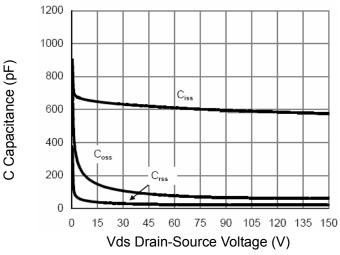


Figure 7 Capacitance vs Vds

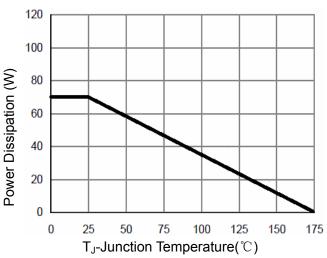


Figure 9 Power De-rating

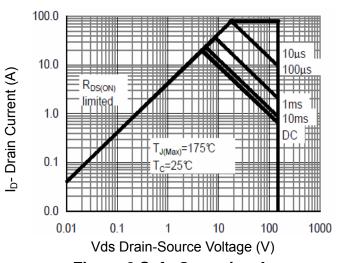


Figure 8 Safe Operation Area

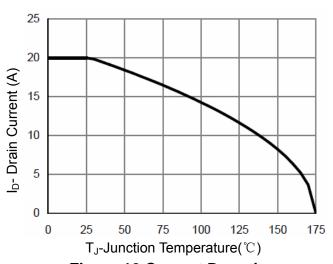
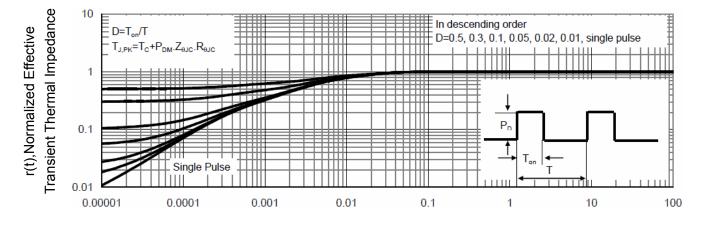


Figure 10 Current De-rating

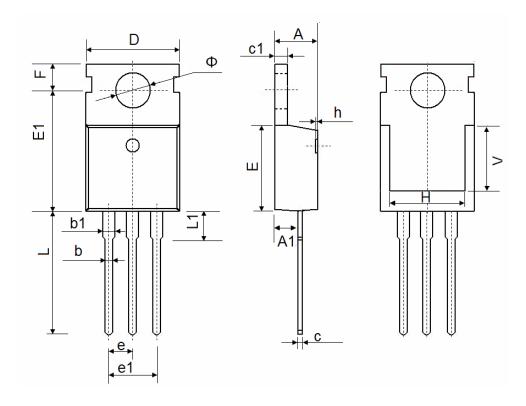


Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



TO-220-3L Package Information



| Symbol | Dimensions | In Millimeters | Dimensions In Inches | | |
|--------|------------|----------------|----------------------|-------|--|
| | Min. | Max. | Min. | Max. | |
| А | 4.400 | 4.600 | 0.173 | 0.181 | |
| A1 | 2.250 | 2.550 | 0.089 | 0.100 | |
| b | 0.710 | 0.910 | 0.028 | 0.036 | |
| b1 | 1.170 | 1.370 | 0.046 | 0.054 | |
| С | 0.330 | 0.650 | 0.013 | 0.026 | |
| c1 | 1.200 | 1.400 | 0.047 | 0.055 | |
| D | 9.910 | 10.250 | 0.390 | 0.404 | |
| Е | 8.9500 | 9.750 | 0.352 | 0.384 | |
| E1 | 12.650 | 12.950 | 0.498 | 0.510 | |
| е | 2.540 | TYP. | 0.100 TYP. | | |
| e1 | 4.980 | 5.180 | 0.196 | 0.204 | |
| F | 2.650 | 2.950 | 0.104 | 0.116 | |
| Н | 7.900 | 8.100 | 0.311 | 0.319 | |
| h | 0.000 | 0.300 | 0.000 | 0.012 | |
| L | 12.900 | 13.400 | 0.508 | 0.528 | |
| L1 | 2.850 | 3.250 | 0.112 | 0.128 | |
| V | 7.500 | 7.500 REF. | | REF. | |
| Ф | 3.400 | 3.800 | 0.134 | 0.150 | |



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